



Market News

600 V CoolMOS™ CFD7 SJ MOSFET pushes the performance boundary to the next level

Munich, Germany – 21 November 2017 – Infineon Technologies AG (FSE: IFX / OTCQX: IFNNY) releases the latest high-voltage Superjunction MOSFET technology, the 600 V CoolMOS™ CFD7 completing the CoolMOS 7 series. This new MOSFET addresses the high power SMPS market for resonant topologies. It offers industry-leading efficiency and reliability in soft switching topologies like LLC and ZVS PSFB. This makes it a perfect fit for high power SMPS applications such as [Servers](#), [Telecom equipment power](#), and [EV charging stations](#).

The 600 V CoolMOS CFD7 succeeds the CoolMOS CFD2. The new MOSFET is up to 1.45 percent more efficient than its predecessor or competitor offerings. It combines all of the advantages of a fast switching technology with high commutation ruggedness, without impacting the easy implementation in the design-in process. The 600 V CoolMOS CFD7 features reduced gate charge (Q_g) and improved turn-off behavior. Additionally, it has a reverse recovery charge (Q_{rr}), which is up to 69 percent lower than competing products in the marketplace. The 600 V CoolMOS CFD7 provides industry-leading solutions for THD and SMD devices, which supports high power density solutions.

Availability

The 600 V CoolMOS CFD7 is available now in mass production and samples can be ordered. More information is available at www.infineon.com/cfd7.

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Media Relations:
Worldwide Headquarters
U.S.A.
Asia
Japan
Investor Relations

Name:
Volker Gieritz
Sian Cummings
Chi Kang David Ong
Yoko Sasaki
EU/APAC/USA/CAN

Phone:
+49 89 234 36572
+1 310 252 7148
+65 6876 3070
+81 3 5745 7340
+49 89 234 26655

Email:
volker.gieritz@infineon.com
sian.cummings@infineon.com
david.ong@infineon.com
yoko.sasaki@infineon.com
investor.relations@infineon.com